# **Signetics**

# 74LS670 Register File

4 x 4 Register File (3-State)

Product Specification

# **Logic Products**

#### **FEATURES**

- Simultaneous and independent Read and Write operations
- Expandable to almost any word size and bit length
- 3-State outputs
- See '170 for open collector version

#### DESCRIPTION

The '670 is a 16-bit 3-State Register File organized as 4 words of 4 bits each. Separate Read and Write Address and Enable inputs are available, permitting simultaneous writing into one word location and reading from another location. The 4-bit word to be stored is presented to four Data inputs. The Write Address inputs (WA and WB) determine the location of the stored word. When the Write Enable (WE) input is LOW, the data is entered into the addressed location. The addressed location remains transparent to the data while the WE is LOW. Data supplied at the inputs will be read out in true (non-inverting) form from the 3-State outputs. Data and Write Address inputs are inhibited when WE is HIGH.

TYPE	TYPICAL PROPAGATION DELAY	TYPICAL SUPPLY CURRENT (TOTAL)
74LS670	25ns	30mA

#### **ORDERING CODE**

PACKAGES	COMMERCIAL RANGE V <sub>CC</sub> = 5V ±5%; T <sub>A</sub> = 0°C to +70°C
Plastic DIP	N74LS670N
Plastic SOL-16	N74LS670D

#### NOTE:

For information regarding devices processed to Military Specifications, see the Signetics Military Products Data Manual.

# INPUT AND OUTPUT LOADING AND FAN-OUT TABLE

PINS	DESCRIPTION	74LS
D <sub>0</sub> - D <sub>3</sub> , W <sub>A</sub> , W <sub>B</sub> , R <sub>A</sub> , R <sub>B</sub>	Inputs	1LSul
WE	înput	2LSul
RE	Input	3LSul
Q <sub>0</sub> – Q <sub>3</sub>	Outputs	10LSul

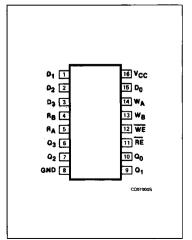
#### NOTE:

A 74LS unit load (LSul) is 20µA IIH and -0.4mA IIL.

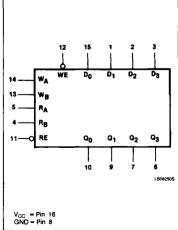
Direct acquisition of data stored in any of the four registers is made possible by individual Read Address inputs ( $R_A$  and  $R_B$ ). The addressed word appears at the four outputs when the Read Enable ( $\overline{RE}$ )

is LOW. Data outputs are in the HIGH impedance "off" state when the Read Enable input is HIGH. This permits outputs to be tied together to increase the word capacity to very large numbers.

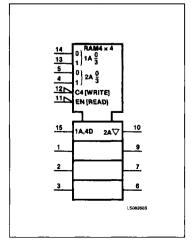
# PIN CONFIGURATION



#### LOGIC SYMBOL



# LOGIC SYMBOL (IEEE/IEC)

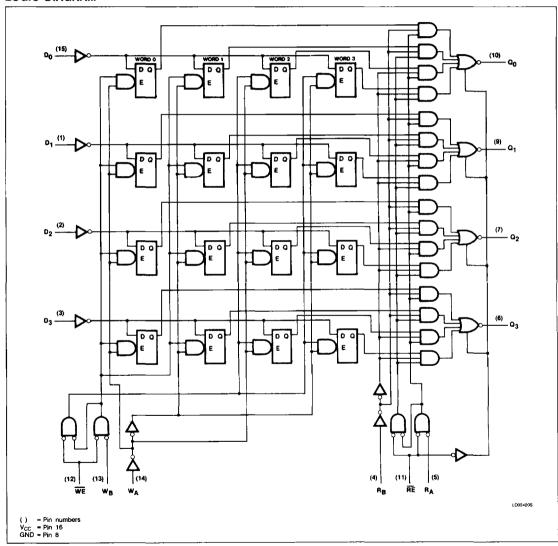


Up to 128 devices can be stacked to increase the word size to 512 locations by tying the 3-State outputs together. Since the limiting factor for expansion is the output HIGH current, further stacking is possible by tying pull-

up resistors to the outputs to increase the I<sub>OH</sub> current available. Design of the Read Enable signals for the stacked devices must ensure that there is no overlap in the LOW levels which would cause more than one output to

be active at the same time. Parallel expansion to generate n-bit words is accomplished by driving the Enable and Address inputs of each device in parallel.

## LOGIC DIAGRAM



# WRITE MODE SELECT TABLE

OPERATING	INP	UTS	INTERNAL
MODE	WE	Dn	LATCHES(8)
Write data	L L	L H	L H
Data latched	н	x	no change

#### NOTE:

## **READ MODE SELECT TABLE**

0050471110		INPUTS	
OPERATING MODE	RE	internal Latches <sup>(b)</sup>	OUTPUT Q <sub>n</sub>
Read	L	H	L H
Disabled	н	Х	(Z)

## NOTE:

- H = HIGH voltage level
- L = LOW voltage level
- X = Don't care
- (Z) = HIGH impedance "off" state.

# ABSOLUTE MAXIMUM RATINGS (Over operating free-air temperature range unless otherwise noted.)

	PARAMETER	74LS	UNIT
V <sub>CC</sub>	Supply voltage	7.0	٧
VIN	Input voltage	-0.5 to +7.0	V
liN	Input current	-30 to +1	mA
Vout	Voltage applied to output in HIGH output state	-0.5 to +V <sub>CC</sub>	٧
TA	Operating free-air temperature range	0 to 70	°C

# RECOMMENDED OPERATING CONDITIONS

	DADAMETED		74LS				
PARAMETER		Min	Nom	Max	UNIT		
V <sub>CC</sub>	Supply voltage	4.75	5.0	5.25	V		
ViH	HIGH-level input voltage	2.0			V		
V <sub>IL</sub>	LOW-level input voltage			+0.8	٧		
lικ	Input clamp current			-18	mA		
Юн	HIGH-level output current			-2.6	mA		
loL	LOW-level output current			8	mA		
TA	Operating free-air temperature	0		70	°C		

a. The Write Address ( $W_A$  and  $W_B$ ) to the "internal latches" must be stable while  $\overline{WE}$  is LOW for conventional operation.

b. The selection of the "internal latches" by Read Address (R<sub>A</sub> and R<sub>B</sub>) are not constrained by WE or RE operation.

# DC ELECTRICAL CHARACTERISTICS (Over recommended operating free-air temperature range unless otherwise noted.)

PARAMETER		DADAMETED TEST CONDITIONS		74LS670				
		1	TEST CONDITIONS <sup>1</sup>			Typ <sup>2</sup>	Max	UNIT
V <sub>OH</sub>	HIGH-level output voltage	V <sub>CC</sub> = MIN, V <sub>IH</sub> = MI		IL = MAX, IOH = MAX	2.4	3.1	_	٧
VI.	LOW/ lovel cutout voltage	V <sub>CC</sub> = MIN, V <sub>II</sub>	= MIN,	I <sub>OL</sub> = MAX		0.35	0.5	٧
VOL	LOW-level output voltage	V <sub>IL</sub> = MAX		I <sub>OL</sub> = 4mA (74LS)		0.25	0.4	٧
$V_{IK}$	Input clamp voltage	V <sub>CC</sub> = MIN, I <sub>I</sub> =	lık				-1.5	>
l <sub>OZH</sub>	Off-state output current, HIGH-level voltage applied	V <sub>CC</sub> = MAX, V <sub>II</sub>	H = MIN, \	V <sub>O</sub> = 2.7V			20	μΑ
lozL	Off-state output current, LOW-level voltage applied	V <sub>CC</sub> = MAX, V <sub>IH</sub> = MIN, V <sub>O</sub> = 0.4V				-20	μΑ	
	Input current at maximum	V <sub>CC</sub> = MAX,	D <sub>0</sub> – D <sub>3</sub> inputs	, W <sub>A</sub> , W <sub>B</sub> , R <sub>A</sub> , R <sub>B</sub>			0.1	mA
lį.	input voltage	V₁ = 7.0V WE input RE input		out			0.2	mA
						0.3	mA	
		V <sub>CC</sub> = MAX,	D <sub>0</sub> – D <sub>3</sub> inputs	B, WA, WB, RA, RB			20	μΑ
ΗΗ	HIGH-level input current	V <sub>1</sub> = 2.7V	WE in	out			40	μΑ
		:	RE input				60	μА
		V <sub>CC</sub> ≈ MAX,	D <sub>0</sub> - D <sub>0</sub> inputs	3, W <sub>A</sub> , W <sub>B</sub> , R <sub>A</sub> , R <sub>B</sub>			-0.4	mA
l <sub>IL</sub>	LOW-level input current	V <sub>1</sub> = 0.4V	WE in	put			-0.8	mA
		RE		out			-1.2	mA
los	Short-circuit output current <sup>3</sup>	V <sub>CC</sub> = MAX		_	-20		-100	mA
lcc	Supply current <sup>4</sup> (total)	V <sub>CC</sub> = MAX				30	50	mA

#### NOTES:

- 1. For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions for the applicable type.
- 2. All typical values are at  $V_{CC} = 5V$ ,  $T_A = 25$ °C.
- 3. Ios is tested with V<sub>OUT</sub> = +0.5V and V<sub>CC</sub> = V<sub>CC</sub> MAX + 0.5V. Not more than one output should be shorted at a time and duration of the short circuit should not exceed one second.
- Measure I<sub>CC</sub> with 4.5V applied to all Data inputs and Read Enable and Write Enable inputs, ground Read Address and Write Address inputs and leave all outputs
  open. This is a worse-case condition.

# AC ELECTRICAL CHARACTERISTICS TA = 25°C, VCC = 5.0V

			74L	S670	j
PARAMETER		TEST CONDITIONS	C <sub>L</sub> = 15pF	UNIT	
			Min Max		
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay Read address to output	Waveform 2		40 45	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay Write enable to output	Waveform 1		45 50	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay Data to output	Waveform 1		45 40	ns
t <sub>PZH</sub>	Enable time to HIGH level	Waveform 3		35	ns
t <sub>PZL</sub>	Enable time to LOW level	Waveform 3		40	ns
t <sub>PHZ</sub>	Disable time from HIGH level	Waveform 3, C <sub>L</sub> = 5pF		50	ns
t <sub>PLZ</sub>	Disable time from LOW level	Waveform 3, C <sub>L</sub> = 5pF		35	ns

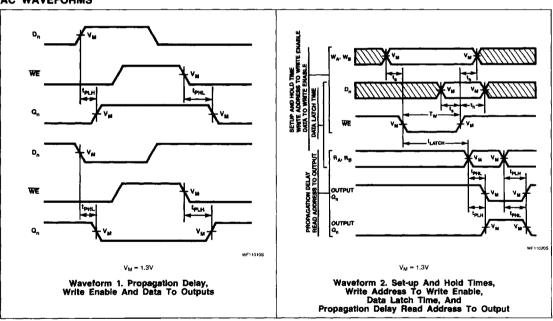
December 4, 1985 5-613

# AC SET-UP REQUIREMENTS TA = 25°C, VCC = 5.0V

	DADANISTED	TEGT COMPUTIONS	74LS670		
	PARAMETER	TEST CONDITIONS	Min	Max	UNIT
tw	Read enable pulse width	Waveform 3	25		ns
tw	Write enable pulse width	Waveform 2, RE = ≤ 0.8V	25		กร
ts	Set-up time, data to positive-going WE	Waveform 2	10		ns
th	Hold time, data to positive-going WE	Waveform 2	15		ns
ts	Set-up time, write address to negative-going WE(c)	Waveform 2	15		ns
th	Hold time, write address to positive-going WE(c)	Waveform 2	5.0		ns
t <sub>latch</sub>	Latch time for new data <sup>(d)</sup>	Waveform 2	25		ns

## NOTES:

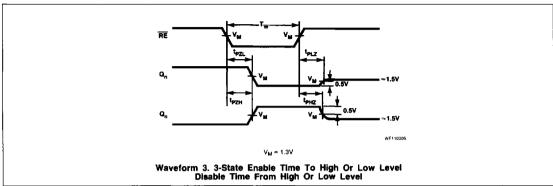
# **AC WAVEFORMS**



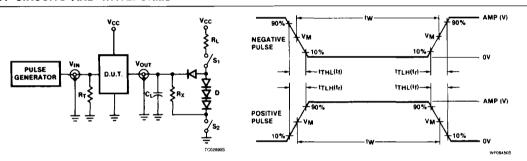
c. Write address set-up time will protect the data written into the previous address. If protection of data in the previous address is not required, ts (write address to WE) can be ignored, as any address selection sustained for the final 30ns of the WE pulse and during th (write address to WE) will result in data being written into that location. Depending on the duration of the input conditions, one or a number of previous addresses may have been written into

d. Latch time is the time allowed for the internal output of the latch to assume the state of new date. This is important only when attempting to read from a location immediately after that location has received new data. This parameter is measured from the falling edge of WE to the rising or falling edge of R<sub>A</sub> or R<sub>B</sub>. RE must be LOW.

# AC WAVEFORMS (Continued)



## TEST CIRCUITS AND WAVEFORMS



Test Circuit For 3-State Outputs

# $V_M = 1.3V$ for 74LS; $V_M = 1.5V$ for all other TTL families. Input Pulse Definition

## SWITCH POSITION

TEST	SWITCH 1	SWITCH 2
t <sub>PZH</sub>	Open	Closed
t <sub>PZL</sub>	Closed	Open
t <sub>PHZ</sub>	Closed	Closed
tPLZ	Closed	Closed

# DEFINITIONS

 $R_L$  = Load resistor to  $V_{CC}$ ; see AC CHARACTERISTICS for value.

C<sub>L</sub> = Load capacitance includes jig and probe capacitance; see AC CHARACTERISTICS for value.

 $R_T$  = Termination resistance should be equal to  $Z_{OUT}$  of Pulse Generators.

D = Diodes are 1N916, 1N3064, or equivalent.

 $R_X = 1k\Omega$  for 74, 74S,  $R_X = 5k\Omega$  for 74LS.

 $t_{\text{TLH.}} \ t_{\text{THL}}$  Values should be less than or equal to the table entries.

· · ·	INPUT PULSE REQUIREMENTS							
FAMILY	Amplitude	Rep. Rate	Pulse Width	t <sub>TLH</sub>	t <sub>THL</sub>			
74	3.0V	1MHz	500ns	7ns	7ns			
74LS	3.0V	1MHz	500ns	15ns	6ns			
74S	3.0V	1 MHz	500ns	2.5ns	2.5ns			